# **Small Signal MOSFET**

30 V, 154 mA, Single, N-Channel, Gate ESD Protection, SC-75

#### Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- Pb-Free Package is Available

#### Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players, Digital Cameras, PDA's, Video Games, Hand-Held Computers, etc.

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Paramo	Symbol	Value	Unit	
Drain-to-Source Voltage		V <sub>DSS</sub>	30	V
Gate-to-Source Voltage	Gate-to-Source Voltage			V
Continuous Drain Current (Note 1)	۱ <sub>D</sub>	154	mA	
Power Dissipation (Note 1)	P <sub>D</sub>	300	mW	
Pulsed Drain Current	I <sub>DM</sub>	618	mA	
Operating Junction and Si	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	
Continuous Source Curren	I <sub>SD</sub>	154	mA	
Lead Temperature for Sole (1/8" from case for 10 s)	ΤL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

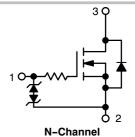
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

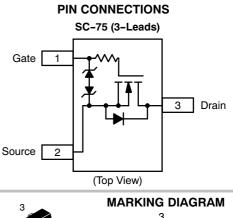


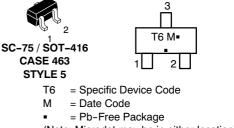
# **ON Semiconductor®**

#### http://onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ @ V <sub>GS</sub>	I <mark>D</mark> MAX (Note 1)
00.14	1.4 Ω @ 4.5 V	154 4
30 V	2.3 Ω @ 2.5 V	154 mA







(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping†
NTA7002NT1	SC-75	3000 Tape & Reel
NTA7002NT1G	SC-75 (Pb-Free)	3000 Tape & Reel

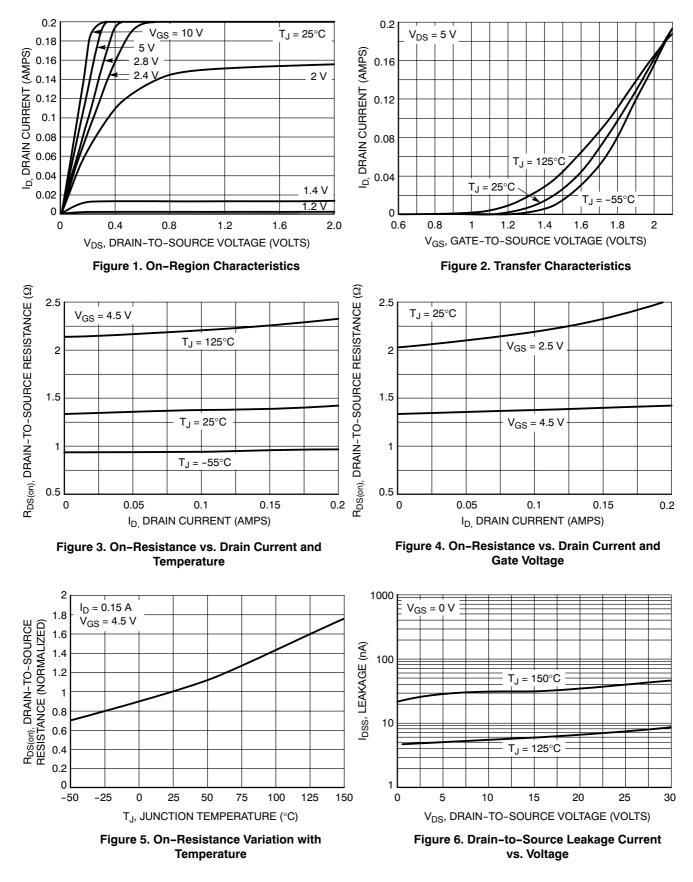
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 100 $\mu$ A	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 30 V			1.0	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 20 V, $T$ = 85 $^{\circ}\mathrm{C}$			1.0	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±10 V			±25	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±5 V			±1.0	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$\begin{array}{c} V_{DS} = 0 \ V, \ V_{GS} = \pm 5 \ V \\ T = 85 \ ^\circ C \end{array}$			±1.0	μΑ
ON CHARACTERISTICS (Note 2)				-		-
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{DS}$ = $V_{GS}$ , $I_D$ = 100 $\mu$ A	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 154 mA		1.4	7.0	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 154 mA		2.3	7.5	
Forward Transconductance	9fs	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 154 mA		80		mS
CAPACITANCES						
Input Capacitance	C <sub>ISS</sub>			11.5	20	pF
Output Capacitance	C <sub>OSS</sub>	V <sub>DS</sub> = 5.0 V, f = 1 MHz, V <sub>GS</sub> = 0 V		10	15	
Reverse Transfer Capacitance	C <sub>RSS</sub>			3.5	6.0	
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time	t <sub>d(ON)</sub>			13		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 5.0 V,		15		ns
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$I_D = 75 \text{ mA}, R_G = 10 \Omega$		98		
Fall Time	t <sub>f</sub>			60		
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 154 mA		0.77	0.9	V

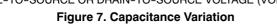
Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperatures.

#### **TYPICAL PERFORMANCE CURVES**



#### 25 1000 F Ciss $T_J = 25^{\circ}C$ V<sub>DD</sub> = 5.0 V I<sub>D</sub> = 75 mA 20 V<sub>GS</sub> = 4.5 V C, CAPACITANCE (pF) C<sub>rss</sub> 100 t<sub>d(off)</sub> 15 t, TIME (ns) E t<sub>f</sub> $\square$ 10 tr Ciss 10 t<sub>d(on)</sub> C<sub>oss</sub> 5 $V_{DS} = 0 V$ V<sub>GS</sub> = 0 V Crss 0 1 5 5 10 15 10 0 20 1 10 100 V<sub>GS</sub> | V<sub>DS</sub> R<sub>G</sub>, GATE RESISTANCE (OHMS) GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

#### **TYPICAL PERFORMANCE CURVES**





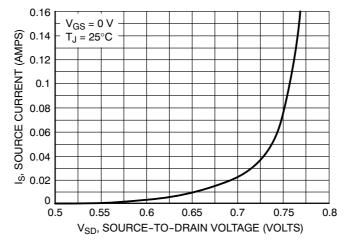
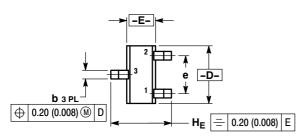
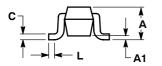


Figure 9. Diode Forward Voltage vs. Current

#### PACKAGE DIMENSIONS

SC-75 / SOT-416 CASE 463-01 ISSUE F





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982

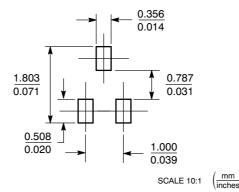
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
Е	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC			0	0.04 BSC	)
L	0.10	0.15	0.20	0.004	0.006	0.008
He	1.50	1.60	1.70	0.061	0.063	0.065



3. DRAIN

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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